

isc Silicon PNP Power Transistor

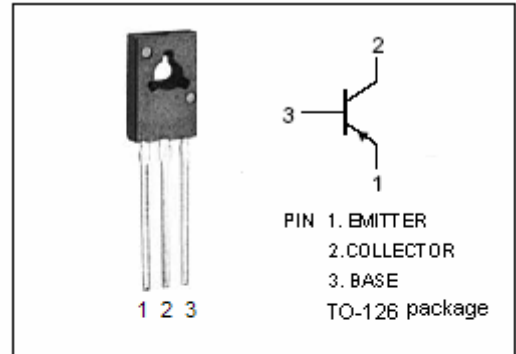
MJE371

DESCRIPTION

- Collector–Emitter Sustaining Voltage—  
:  $V_{CEO(SUS)} = -40V$
- DC Current Gain—  
:  $h_{FE} = 40(\text{Min}) @ I_C = -1A$
- Complement to Type MJE521

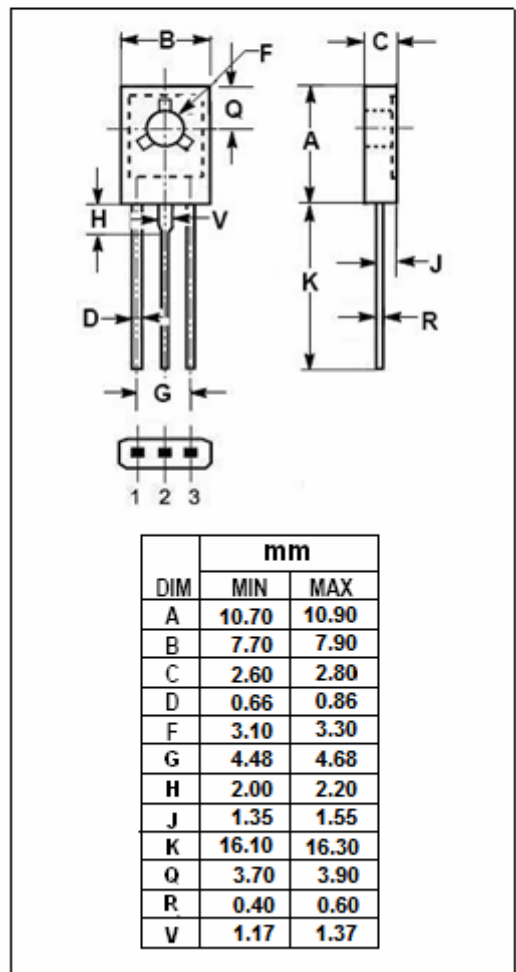
APPLICATIONS

- Designed for use in general-purpose amplifier and switching circuits.
- Recommended for use in 5~20 Watt audio amplifiers utilizing complementary symmetry circuitry.



ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-40	V
$V_{CEO}$	Collector-Emitter Voltage	-40	V
$V_{EBO}$	Emitter-Base Voltage	-4	V
$I_C$	Collector Current-Continuous	-4	A
$I_{CM}$	Collector Current-peak	-8	A
$I_B$	Base Current	-2	A
$P_C$	Collector Power Dissipation $T_C=25^{\circ}C$	40	W
$T_j$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature Range	-65~150	$^{\circ}C$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	3.12	$^{\circ}C/W$

**isc Silicon PNP Power Transistor****MJE371****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C = -100\text{mA}; I_B = 0$	-40		V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -40\text{V}; I_E = 0$		-100	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -4\text{V}; I_C = 0$		-100	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -1\text{V}$	40		